1A, 200V-1000V High Efficient Surface Mount Rectifiers

FEATURES

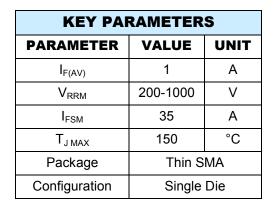
- Glass passivated junction chip
- Ideal for automated placement
- Low power loss, high efficiency
- Fast switching for high efficiency
- Low profile package
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Freewheeling application
- Switching mode converters and inverters, computer and telecommunication.

MECHANICAL DATA

- Case: Thin SMA
- Molding compound meets UL 94V-0 flammability rating
- Moisture sensitivity level: level 1, per J-STD-020
- Terminal: Pure tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 0.029 g (approximately)







Thin SMA

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)							
PARAMETER	SYMBOL	HS1DAL	HS1GAL	HS1JAL	HS1KAL	HS1MAL	UNIT
Marking code on the device		HS1DAL	HS1GAL	HS1JAL	HS1KAL	HS1MAL	
Repetitive peak reverse voltage	V _{RRM}	200	400	600	800	1000	V
Reverse voltage, total rms value	V _{R(RMS)}	140	280	420	560	700	V
Forward current	I _{F(AV)}			1			А
Surge peak forward current, single half sine-wave				35			А
superimposed on rated load per diode 1.0 ms at T _A = 25°C	IFSM			90			А
Junction temperature	TJ			-55 to +150)		°C
Storage temperature	T _{STG}			-55 to +150)		°C



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-lead thermal resistance	R _{ejl}	29	°C/W
Junction-to-ambient thermal resistance	R _{eja}	51	°C/W
Junction-to-case thermal resistance	R _{eJC}	22	°C/W

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
		I _F = 0.5A, T _J = 25°C		0.80	-	V
		I _F = 1A, T _J = 25°C		0.85	1.00	V
	HS1DAL	I _F = 0.5A, T _J = 125°C		0.65	-	V
		I _F = 1A, T _J = 125°C		0.71	0.80	V
		I _F = 0.5A, T _J = 25°C		0.84	-	V
		I _F = 1A, T _J = 25°C		0.91	1.30	V
	HS1GAL	I _F = 0.5A, T _J = 125°C		0.68	-	V
		I _F = 1A, T _J = 125°C		0.76	0.86	V
Forward voltage per diode ⁽¹⁾		I _F = 0.5A, T _J = 25°C	V _F	0.92	-	V
		I _F = 1A, T _J = 25°C		1.02	1.70	V
	HS1JAL	I _F = 0.5A, T _J = 125°C		0.73	-	V
		I _F = 1A, T _J = 125°C		0.83	1.02	V
	HS1KAL HS1MAL	I _F = 0.5A, T _J = 25°C		1.32	-	V
		I _F = 1A, T _J = 25°C		1.49	1.70	V
		I _F = 0.5A, T _J = 125°C		0.98	-	V
		I _F = 1A, T _J = 125°C		1.16	1.39	V
Reverse current @ rated V _R per diode ⁽²⁾		T _J = 25°C	- I _R	-	1	μA
		T _J = 125°C		-	35	μA
	HS1DAL HS1GAL		t _{rr}	-	50	ns
Reverse recovery time	HS1JAL HS1KAL HS1MAL	I _F =0.5A,I _R =1.0A, Irr=0.25A		-	75	ns
	HS1DAL		CJ	20	-	pF
Junction capacitance per diode	HS1GAL			17	-	pF
	HS1JAL	1 MHz, V _R =4.0V		13	-	pF
	HS1KAL HS1MAL			8	-	pF

Notes:

(1) Pulse test with PW=0.3 ms

(2) Pulse test with PW=30 ms



ORDERING INFORMATION			
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING	
HS1xAL M3G	Thin SMA	3,500 / 7" reel	
HS1xAL M2G	Thin SMA	14,000 / 13" reel	

Notes:

(1) "x" defines voltage from 200V(HS1DAL) to 1000V(HS1MAL)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

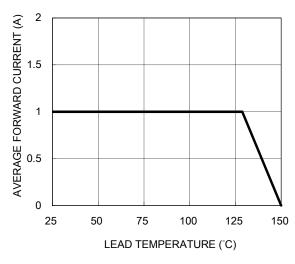
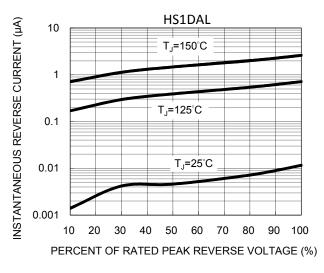
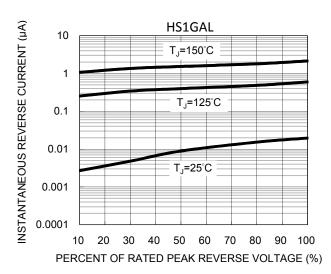


Fig.3 Typical Reverse Characteristics







100 HS1DAL HS1GAL HS1GAL HS1JAL HS1(K)MAL HS1(K)MAL f=1.0MHz Vsig=50mVp-p 1 1 1 10 REVERSE VOLTAGE (V)

Fig.2 Typical Junction Capacitance

Fig.4 Typical Forward Characteristics

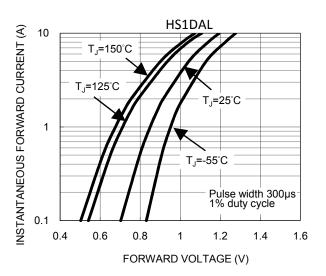
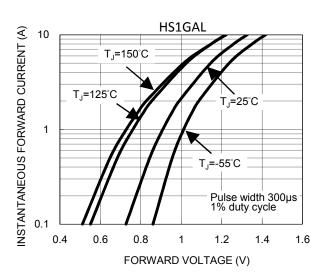


Fig.6 Typical Forward Characteristics





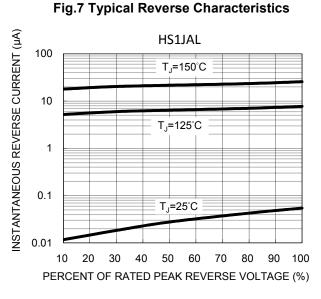
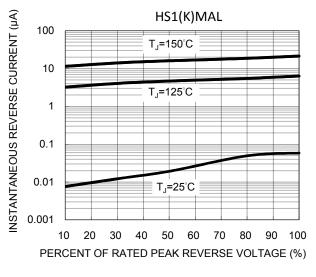


Fig.9 Typical Reverse Characteristics



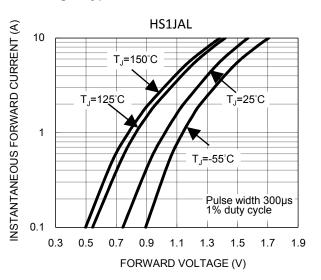
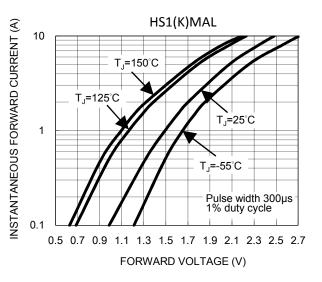


Fig.8 Typical Forward Characteristics

Fig.10 Typical Forward Characteristics



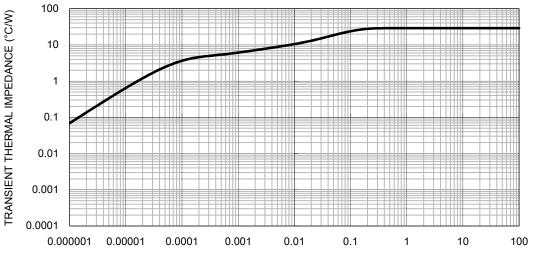


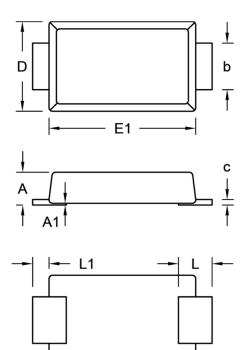
Fig.11 Typical Transient Thermal Impedance

PULSE DURATION (s)



Thin SMA

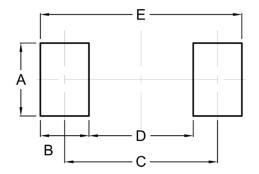
TAIWAN SEMICONDUCTOR



DIM.	Unit (mm)		Unit	(inch)	
	Min.	Max.	Min.	Max.	
A	0.90	1.00	0.035	0.039	
A1	0.00	0.10	0.000	0.004	
b	1.25	1.45	0.049	0.057	
с	0.10	0.22	0.004	0.009	
D	2.50	2.70	0.098	0.106	
E	5.05	5.35	0.199	0.211	
E1	4.15	4.35	0.163	0.171	
L	0.75	1.20	0.030	0.047	
L1	0.30	0.60	0.012	0.024	

SUGGESTED PAD LAYOUT

— E -



Symbol	Unit (mm)	Unit (inch)
А	2.10	0.083
В	1.40	0.055
С	4.40	0.173
D	3.00	0.118
E	5.80	0.228

MARKING DIAGRAM



P/N	= Marking Code
YW	= Date Code
F	= Factory Code



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